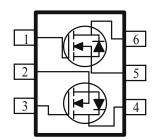
## N-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$r_{\mathrm{DS(on)}} \ \mathrm{m}(\Omega) \qquad \qquad \mathrm{I_D(A)}$			
30	$63 @ V_{GS} = 4.5V$	3.5		
	$110 @ V_{GS} = 2.5V$	3.0		

- Low r<sub>DS(on)</sub> provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe TSOP-6 saves board space
- Fast switching speed
- High performance trench technology





ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Limit	Units			
Drain-Source Voltage			30	V		
Gate-Source Voltage	$V_{GS}$	±12	V			
	$T_A=25^{\circ}C$		3.5			
Continuous Drain Current <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	1D	2.8	A		
Pulsed Drain Current <sup>b</sup>			16			
Continuous Source Current (Diode Conduction) <sup>a</sup>	ontinuous Source Current (Diode Conduction) <sup>a</sup>			Α		
D a	$T_A=25^{\circ}C$	D	1.3	w		
Power Dissipation <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	LD	0.8	VV		
Operating Junction and Storage Temperature Range			-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
a	t <= 10 sec	D	100	°C/W		
Maximum Junction-to-Ambient <sup>a</sup>	Steady-State	$R_{ heta JA}$	166	°C/W		

1

## Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Analog Power AM3932N

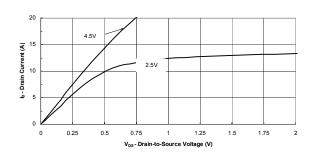
• • • • • • • • • • • • • • • • • • • •		ESS OTHERWISE NOTED)	Limits				
Parameter	Symbol	Test Conditions			Max	Unit	
Static			IVIIII	Тур	Max		
	17	V - V I - 250 :: A	0.7		ı	V	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	0.7		. 100	<u> </u>	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = 12 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
	D33	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25		
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	6			A	
D : G		$V_{GS} = 4.5 \text{ V}, I_D = 3.5 \text{ A}$			63	mΩ	
Drain-Source On-Resistance <sup>A</sup>	<sup>1</sup> DS(on)	$V_{GS} = 2.5 \text{ V}, I_D = 3 \text{ A}$			110		
Forward Tranconductance <sup>A</sup>	$g_{\mathrm{fs}}$	$V_{DS} = 15 \text{ V}, I_D = 3.5 \text{ A}$		6.9		S	
Diode Forward Voltage	$V_{\mathrm{SD}}$	$I_S = 2.3 \text{ A}, V_{GS} = 0 \text{ V}$		0.8		V	
Dynamic <sup>b</sup>					•	•	
Total Gate Charge	$Q_{g}$	V = 15 V V = 4.5 V		6.3			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$ $I_{D} = 3.5 \text{ A}$		0.9		nC	
Gate-Drain Charge	$Q_{gd}$			1.9		1	
Input Capacitance	C <sub>iss</sub>			265			
Output Capacitance	$C_{oss}$	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{MHz}$		54		pF	
Reverse Transfer Capacitance	$C_{rss}$			24		Ì	
Turn-On Delay Time	$t_{d(on)}$			16			
Rise Time	$t_{\rm r}$	$V_{DD} = 25 \text{ V}, R_L = 25 \Omega, I_D = 1 \text{ A},$		5			
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}$		23		nS	
Fall-Time	$t_{\mathrm{f}}$			3		Î	

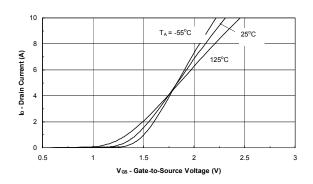
### Notes

- a. Pulse test:  $PW \le 300us duty cycle \le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

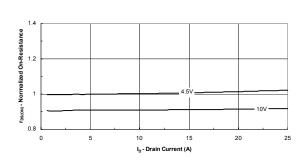
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# Typical Electrical Characteristics (N-Channel)

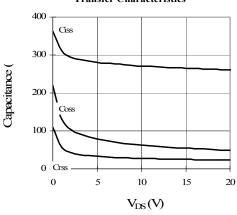




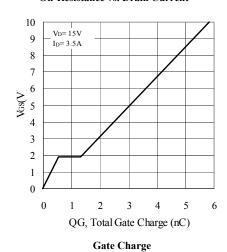
**Output Characteristics** 



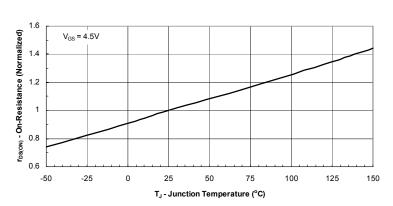
**Transfer Characteristics** 



On-Resistance vs. Drain Current

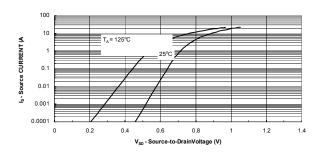


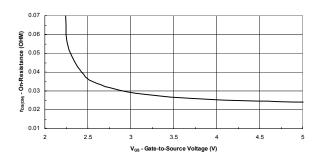
Capacitance



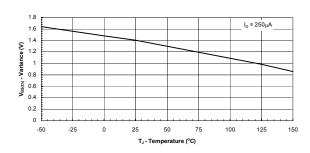
On-Resistance vs. Junction Temperature

## Typical Electrical Characteristics (N-Channel)

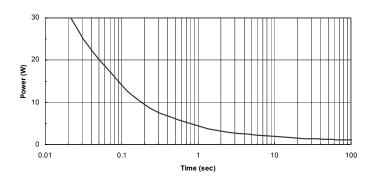


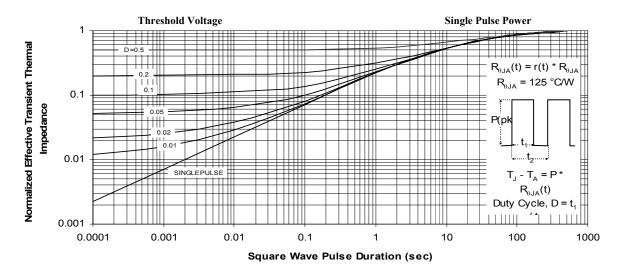


#### Source-Drain Diode Forward Voltage



## On-Resistance vs.Gate-to Source Voltage

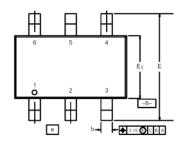


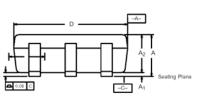


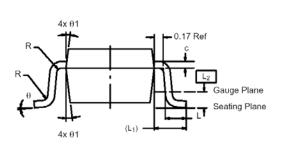
Normalized Thermal Transient Impedance, Junction-to-Ambient

# Package Information

TSOP-6: 6LEAD







	MILLIMETERS INCHES				;	
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.91	-	1.10	0.036	-	0.043
A <sub>1</sub>	0.01	-	0.10	0.0004	_	0.004
A <sub>2</sub>	0.84	_	1.00	0.033	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
С	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067
е	1.00 BSC			0.0394 BSC		
L	0.35	_	0.50	0.014	-	0.020
L <sub>1</sub>	0.60 Ref			0.024 Ref		
L <sub>2</sub>	0.25 BSC			0.010 BSC		
R	0.10	_	_	0.004	_	_
θ	0°	4°	8°	0°	4°	8°
$\theta_1$	7° Nom			7° Nom		